

# **A Switched Decoupling Capacitor Circuit for On-Chip Supply Resonance Damping**

**Jie Gu, Hanyong Eom and Chris H. Kim**

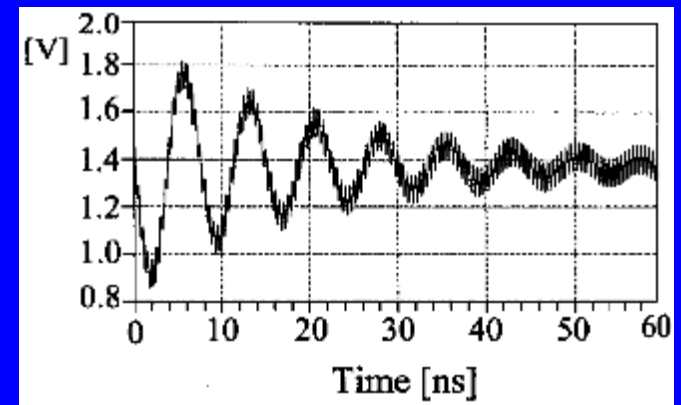
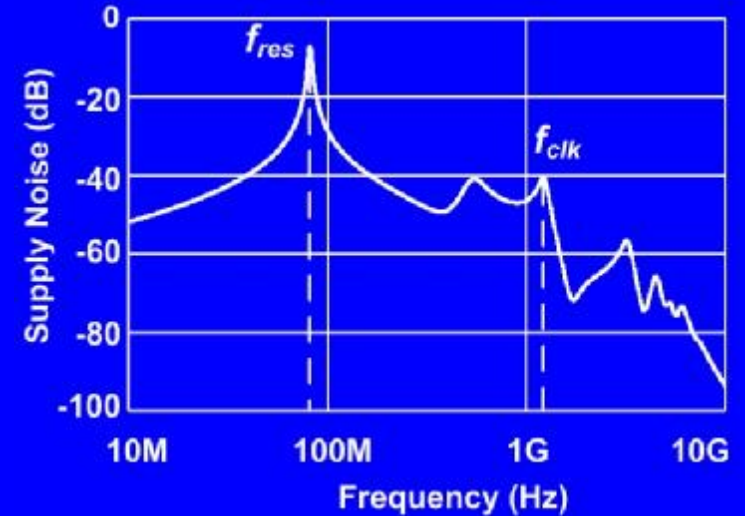
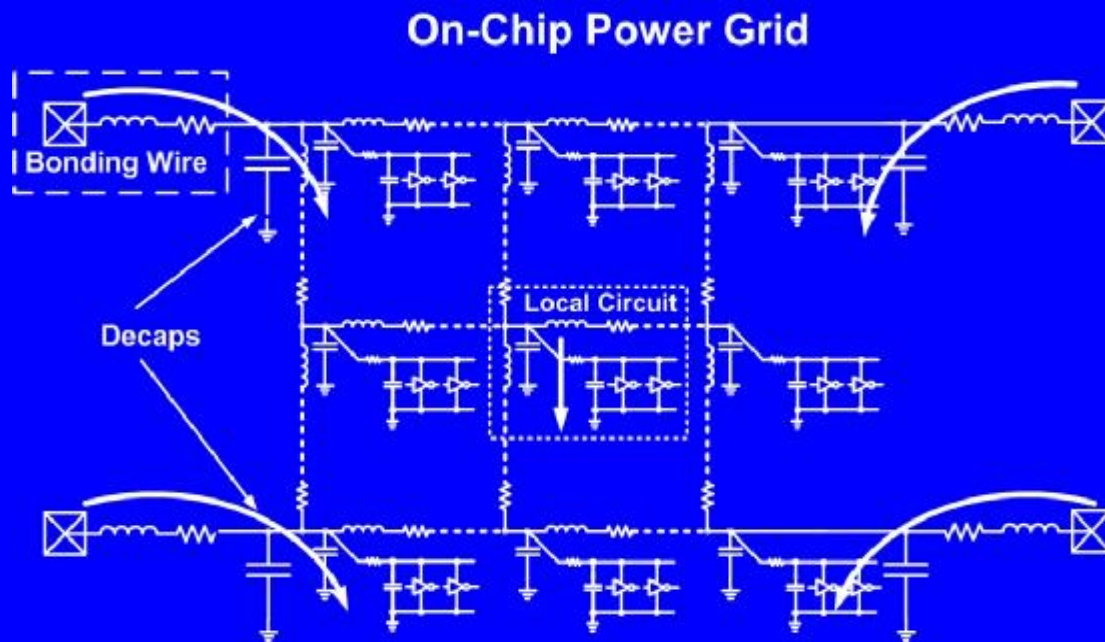
***Department of Electrical and Computer Engineering  
University of Minnesota, Minneapolis***

***jiegu@umn.edu  
<http://www.umn.edu/~chriskim>***

# Outline

- **Introduction to resonant supply noise**
- **Proposed switched decap circuit**
- **Simulated supply noise suppression**
- **Test chip implementation**
- **Supply noise measurement results**
- **Conclusion**

# IC Power Supply: Underdamped RLC Network

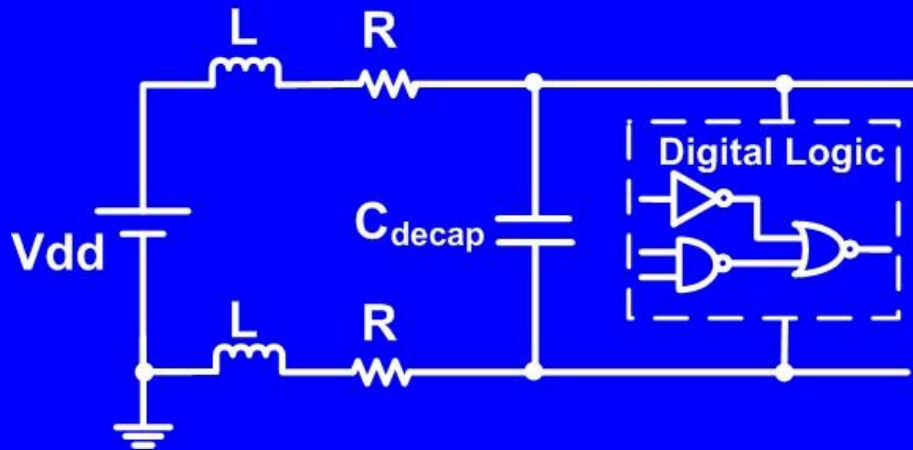


N. Na, IBM, ECTC 2004

- Resonant noise exhibits large magnitude and long duration
- Causes timing violation, clock skew and reliability issue
- Excited by  $\mu$ P loop operation or sudden current spike

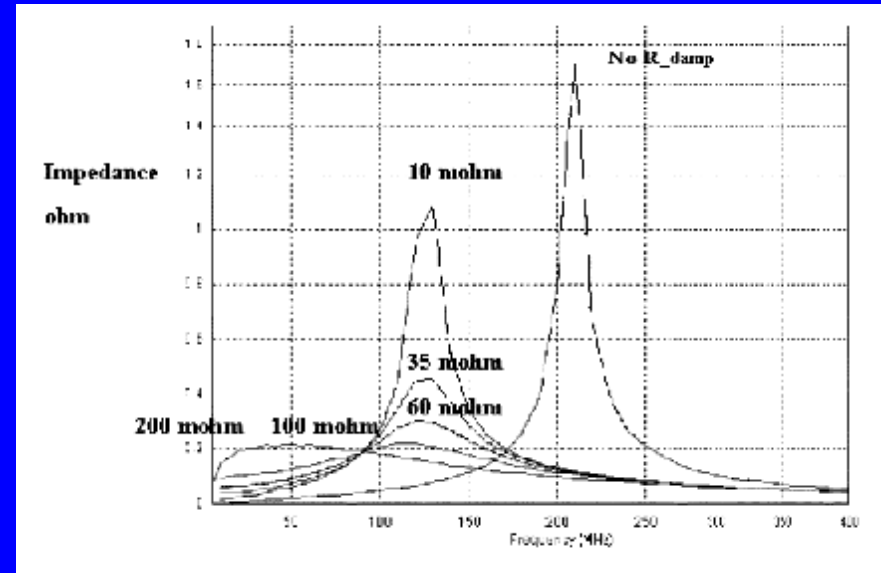
# Previous Passive Damping Techniques

## Add on-chip decap



$$Q = \frac{1}{R_{\text{wire}}} \cdot \sqrt{\frac{L}{C}}$$

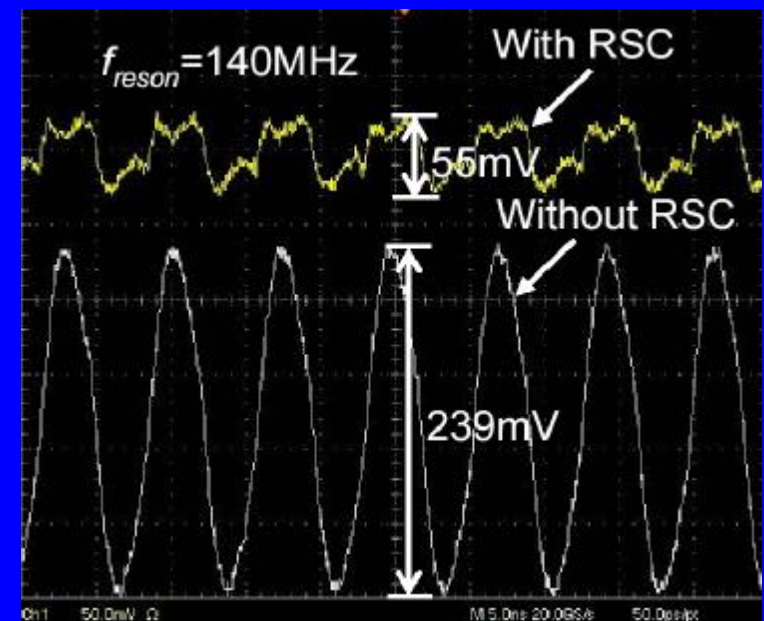
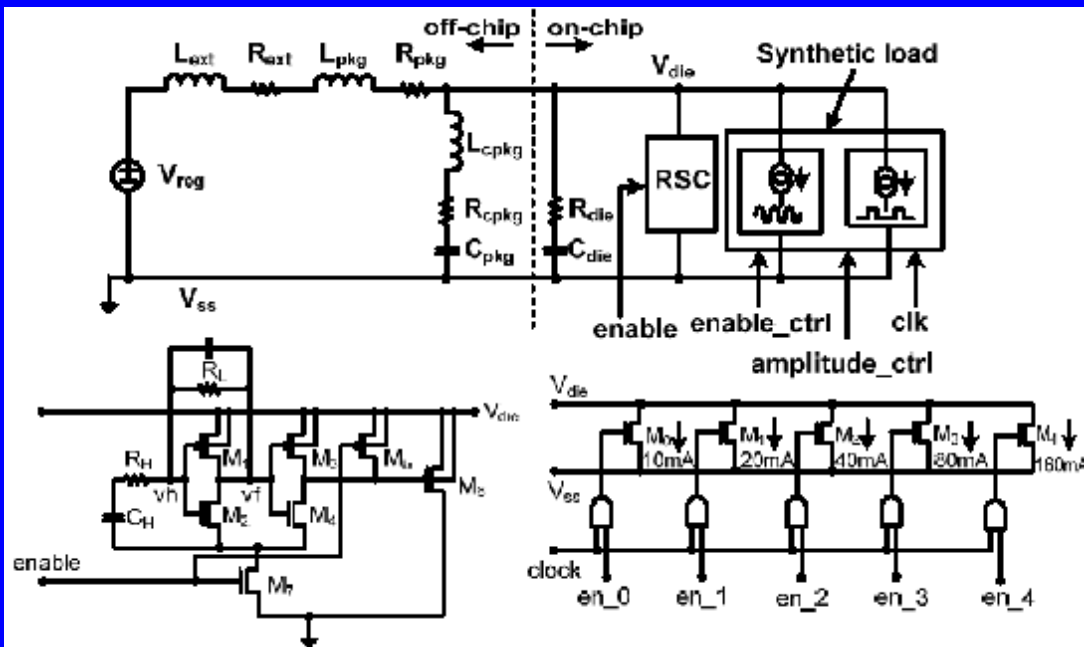
## Add on-chip resistance



G. Ji, et al., Intel, T. Adv. Packaging, 2005

- Increase R and C to bring down the Q factor
- Decap consumes large area and gate leakage
- Resistive damping worsens IR drop

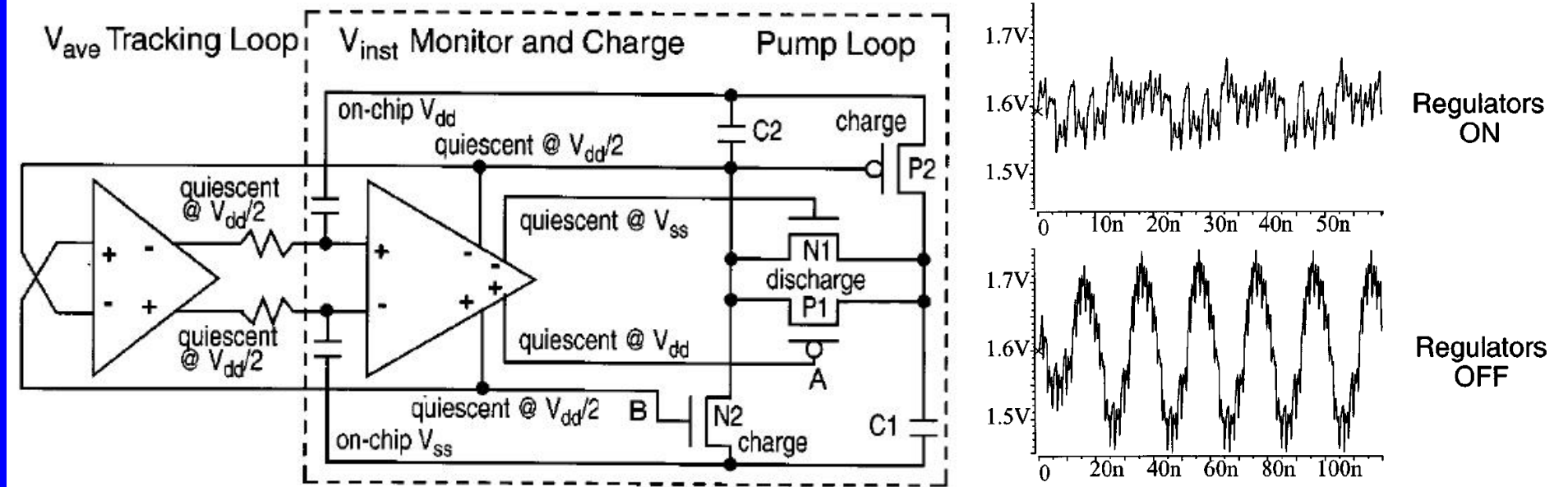
# Previous Active Damping Techniques



J. Xu et al., Intel, ISSCC 2007

- Detect resonant noise and clamp the overshoot
- 1mA static current per 3mA load
- Hard to control trip points under PVT variation
- Only compensates voltage overshoot

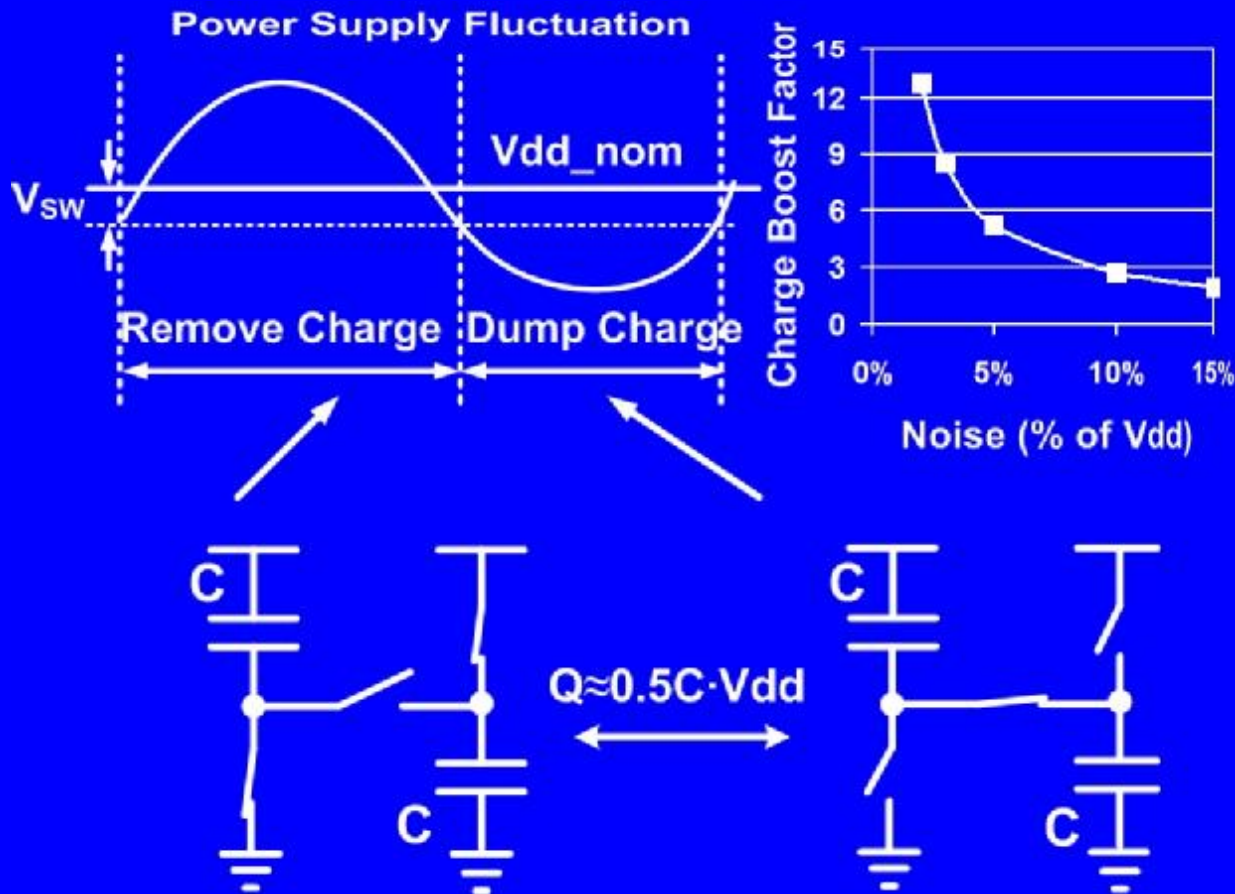
# Previous Active Damping Techniques



M. Ang et al., Sun Microsystems, ISSCC 2000

- **Switching decaps to boost the total charge**
- **5mA quiescent current per regulator**
- **Limited swing and PVT sensitivity in opamp**

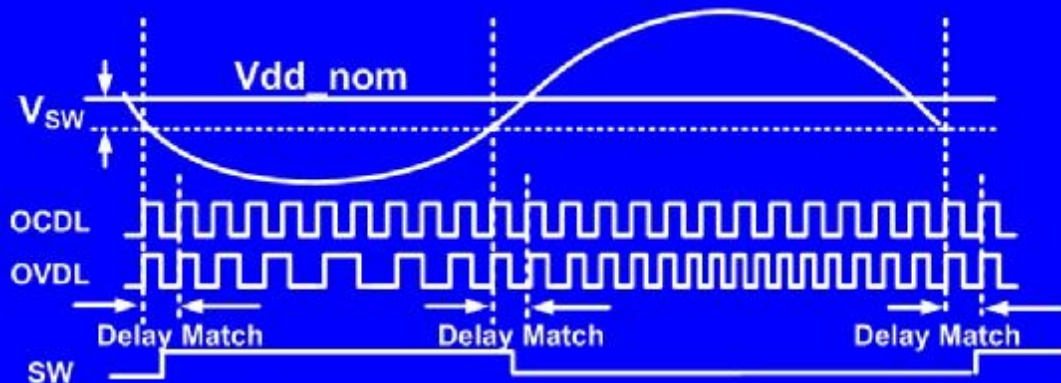
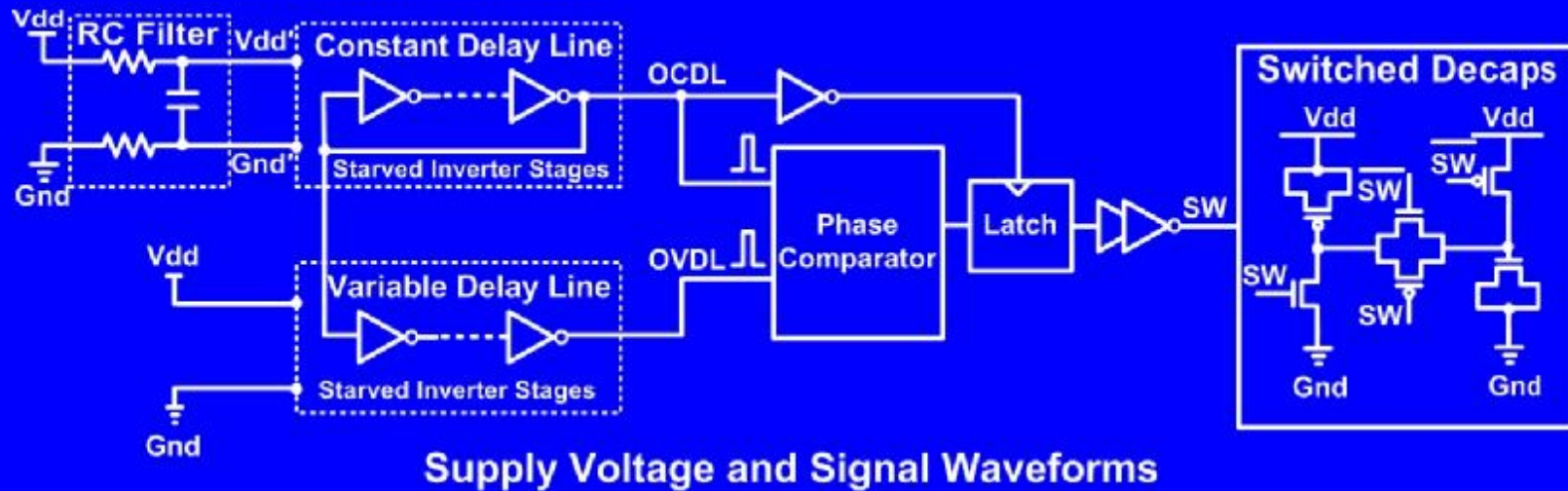
# Principle of Switched Decap Circuit



- $Q_{swdecap} = 0.5C \cdot V_{dd} + C \cdot \Delta V_{dd} / 2$
- $Q_{pdecap} = 2C \cdot \Delta V_{dd}$
- **5–13X charge boosting factor (i.e.  $Q_{swdecap} / Q_{pdecap}$ )**



# Proposed Digital Switched Decap

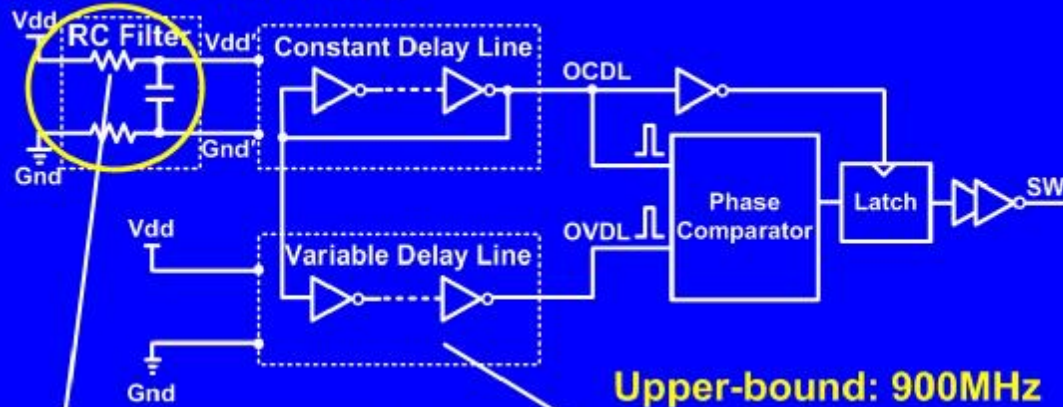


- **Digital resonant detection circuit**
  - Simple implementation for digital ICs
  - Low static power
- **Programmable  $V_{SW}$ , PVT insensitive design**

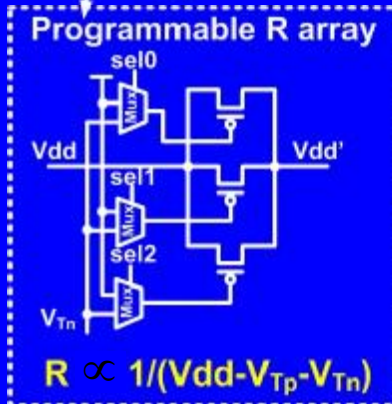


# Bandpass and PVT Insensitive Design

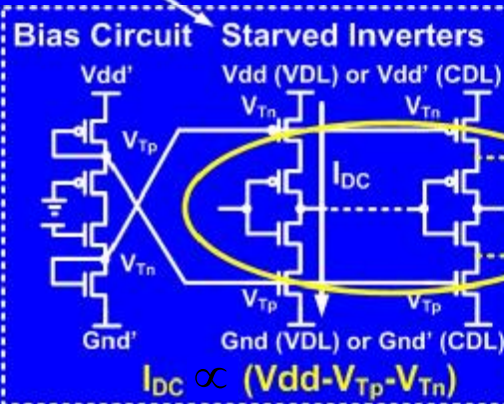
Lower-bound: 10MHz



Upper-bound: 900MHz



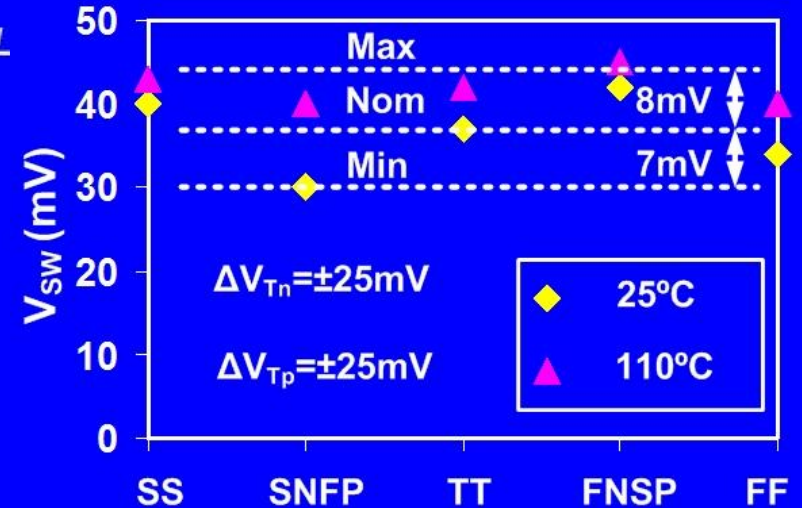
$$R \propto 1/(V_{dd}-V_{Tp}-V_{Tn})$$



$$I_{DC} \propto (V_{dd}-V_{Tp}-V_{Tn})$$

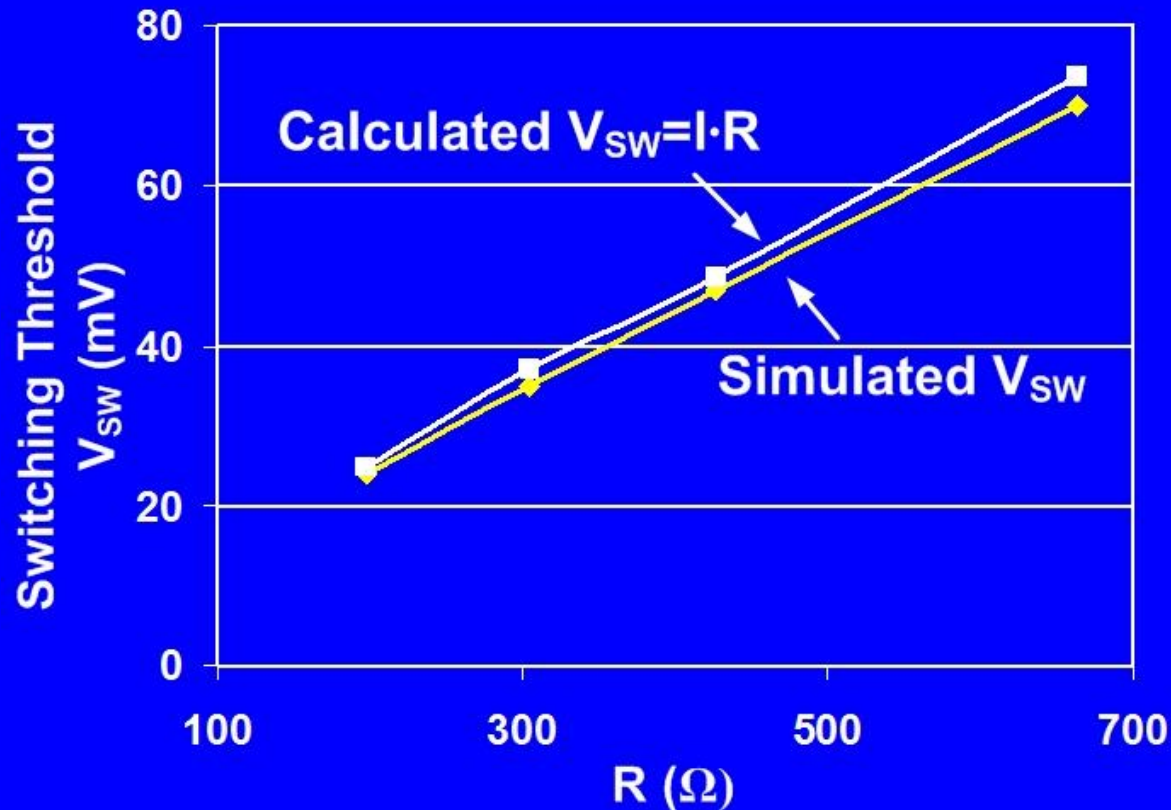
$$V_{SW} = I_{DC} \cdot R \approx \text{Constant}$$

Add small cap to reduce the higher-bound to 500MHz



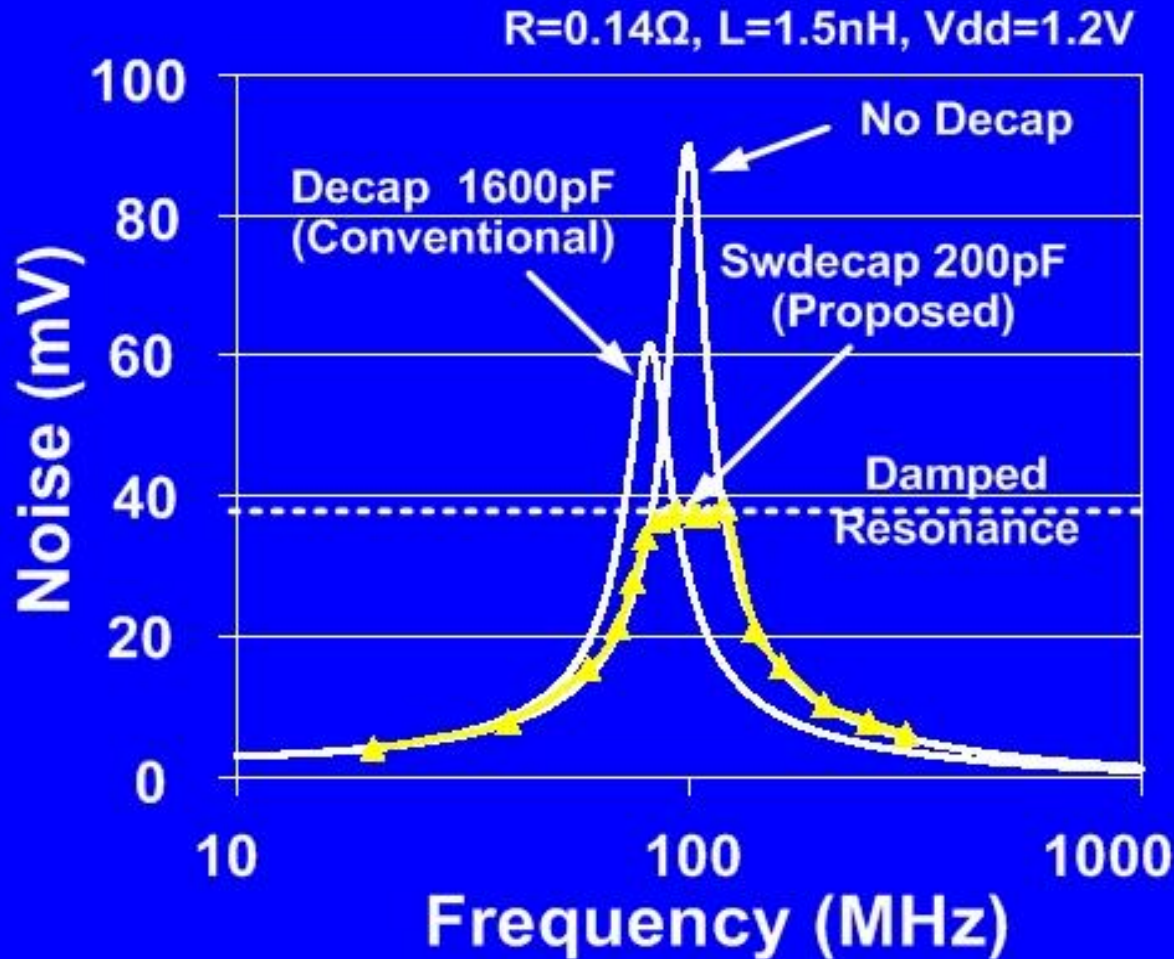
- RC circuit & delay line realize bandpass filter
- 8mV worst-case  $V_{SW}$  variation

# Adjustability of Switching Threshold $V_{sw}$



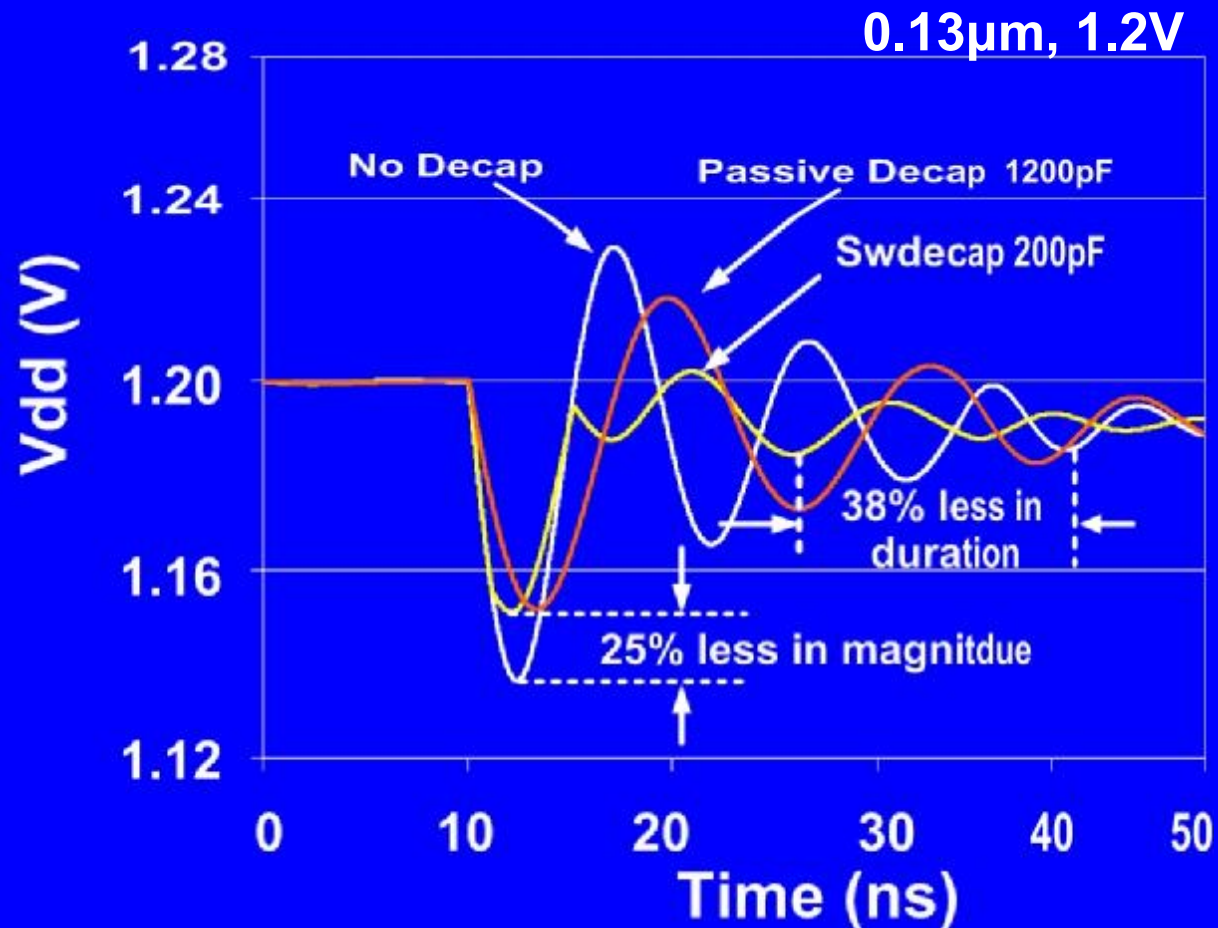
- $V_{sw}$  can be adjusted to avoid unnecessary switching
- $V_{sw}$  is approximately proportional to R value
- R implemented using a programmable MOSFET array

# Simulated Switched Decap Performance



- Resonance is suppressed by 7dB
- More than 8X decap boost for resonant damping

# Simulated First-droop Regulation

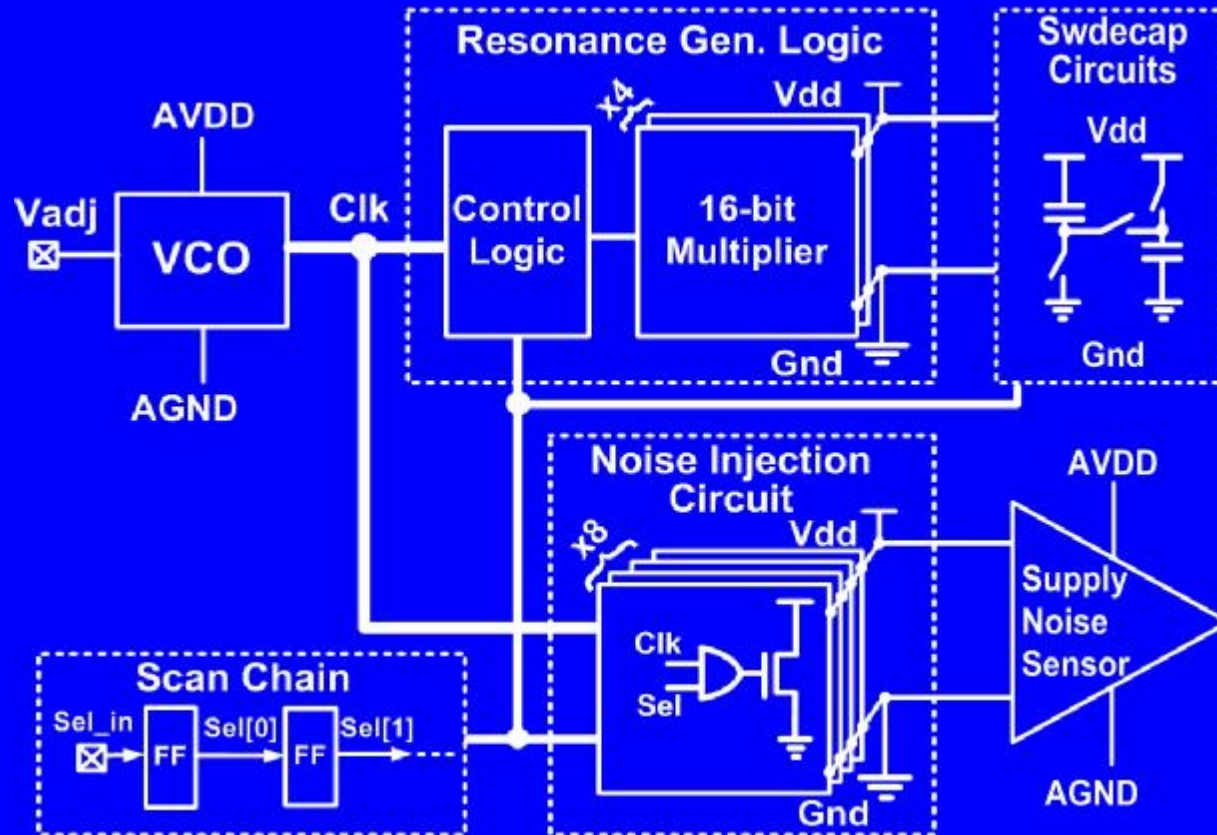


- Both magnitude and oscillation time are reduced for first-droop noise
- 6X+ decap boost compared with passive decap



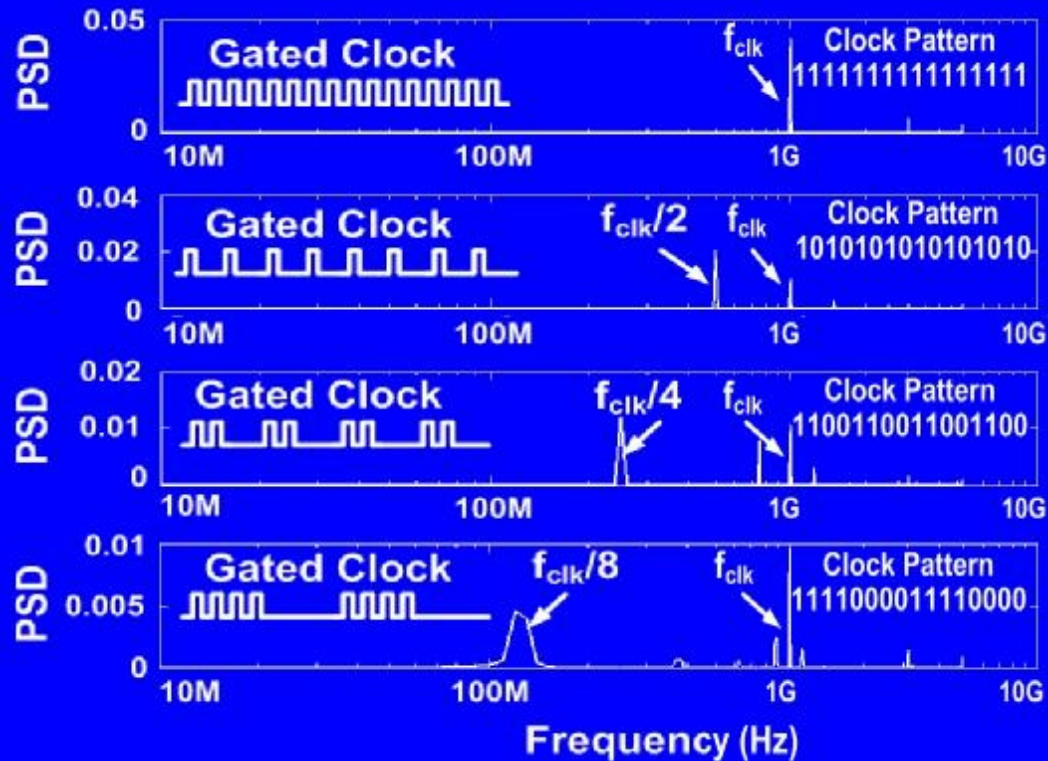
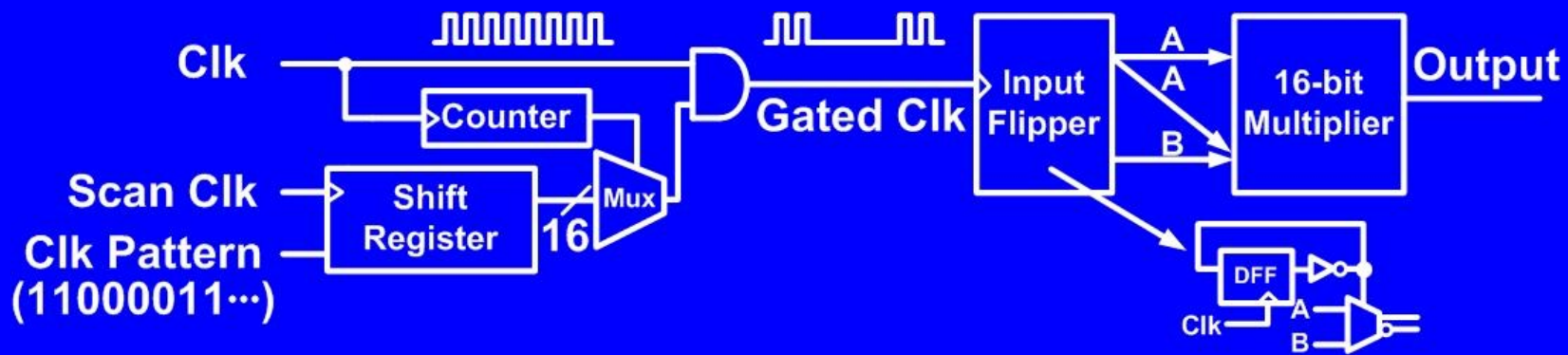
# Test Chip Organization

0.13 $\mu$ m, 1.2V



- Two types of noise generation circuits
- Selection of swdecap value: 100pF, 200pF, 300pF
- On-chip sensor to measure differential noise

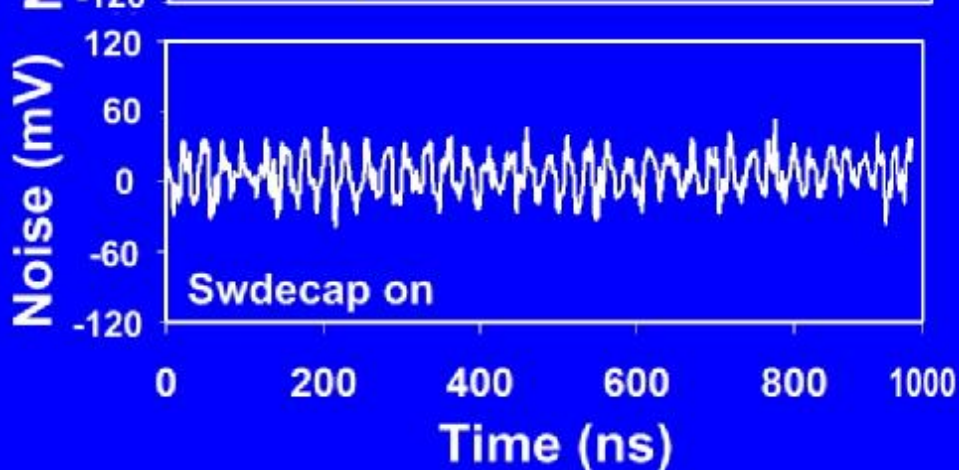
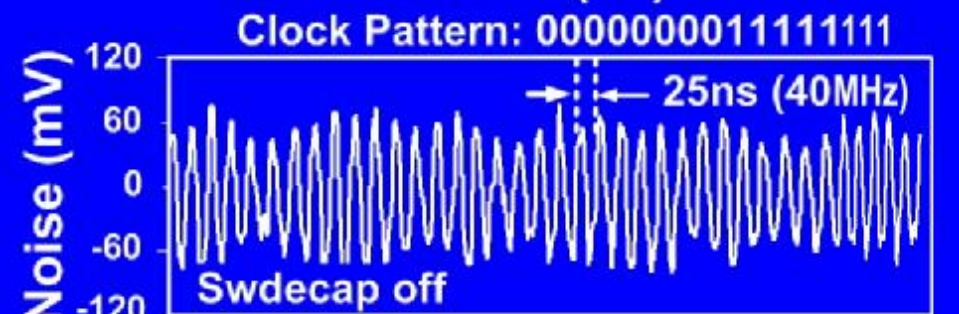
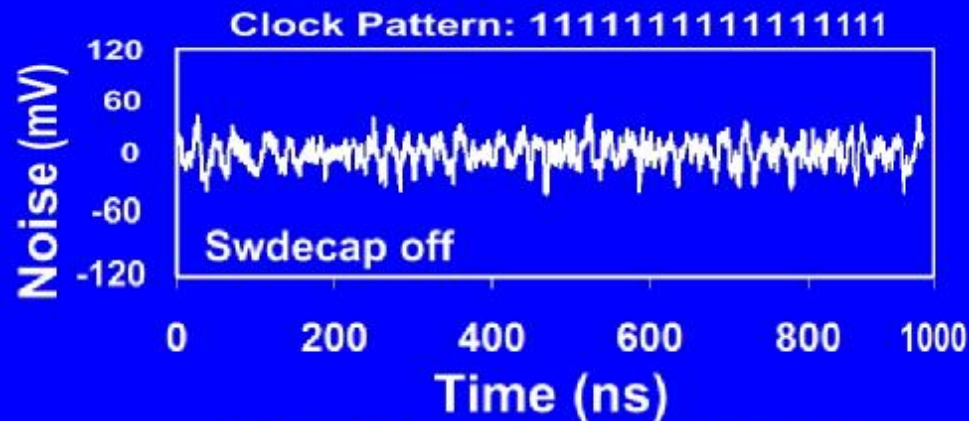
# Resonance Generation Logic



- Creates harmonics at resonant frequency

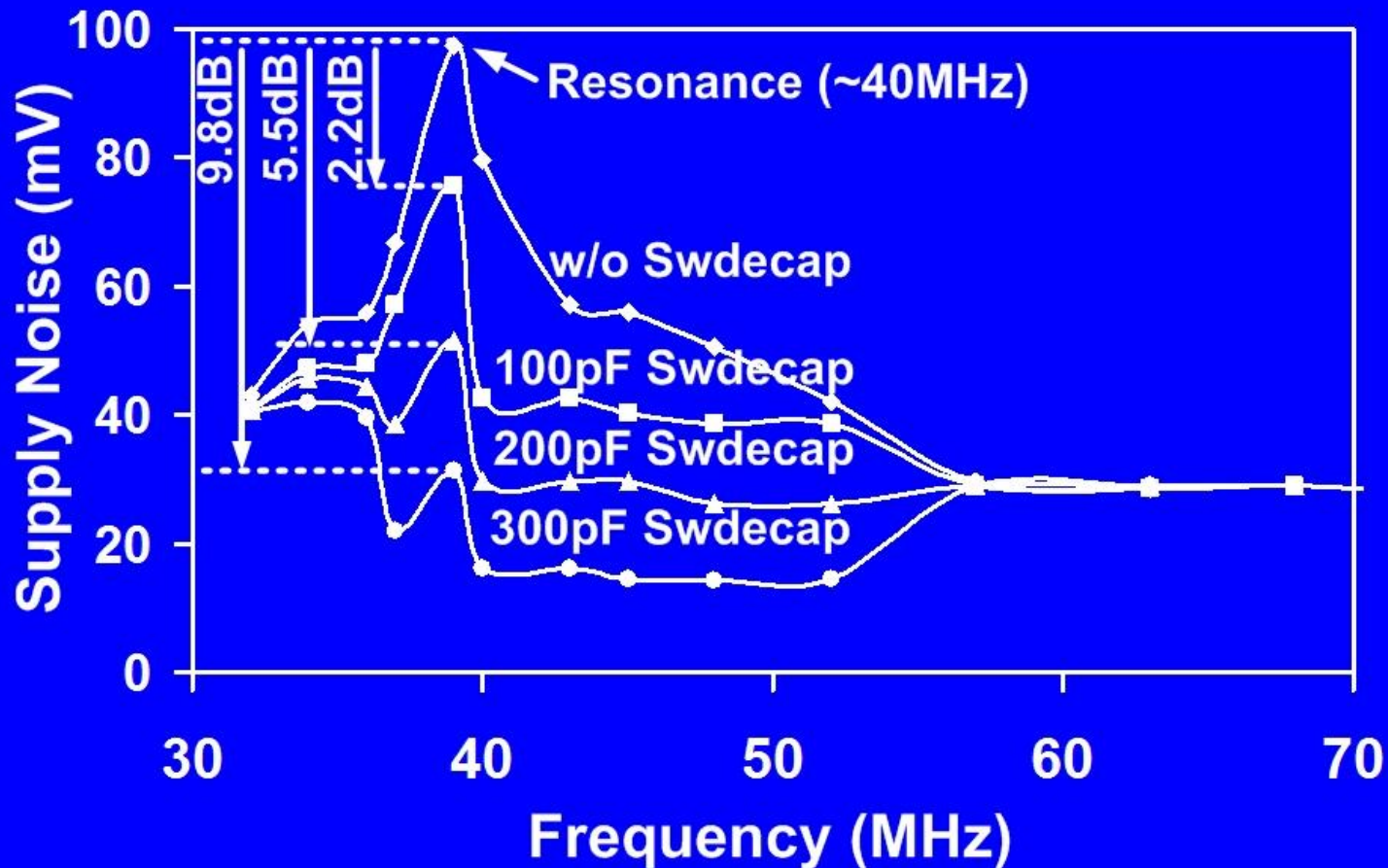


# Supply Noise Measurements



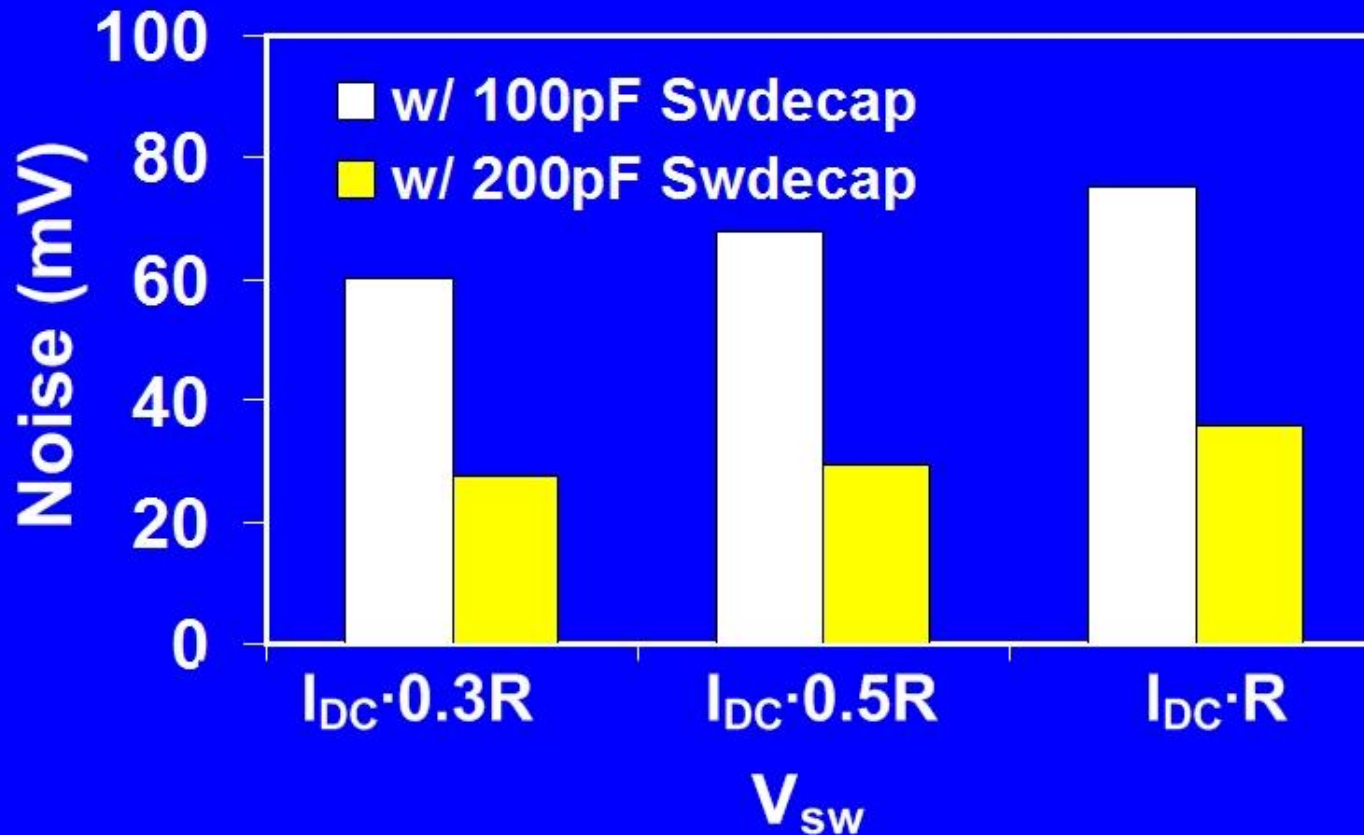
- 640MHz clock gated by 1/16
- 5.5dB noise reduction using 200pF swdecap
- $f_{res}$  at 40MHz lower than expected due to package inductance

# Frequency Domain Measurements



- 9.8dB suppression using 300pF swdecap
- No significant impact on non-resonant frequency noise

# Adjusting Switching Threshold



- Noise magnitude more sensitive to swdecap value than V<sub>sw</sub>

# Comparison with Passive Damping

Swdecap Value	Resonant Suppression	Equiv. Passive Decap	Decap Boost	Equiv. Damp. Resistance
100pF	2.2dB	500pF	5X	0.1 $\Omega$
200pF	5.5dB	1500pF	7.5X	0.4 $\Omega$
300pF	9.8dB	3500pF	11X	1 $\Omega$

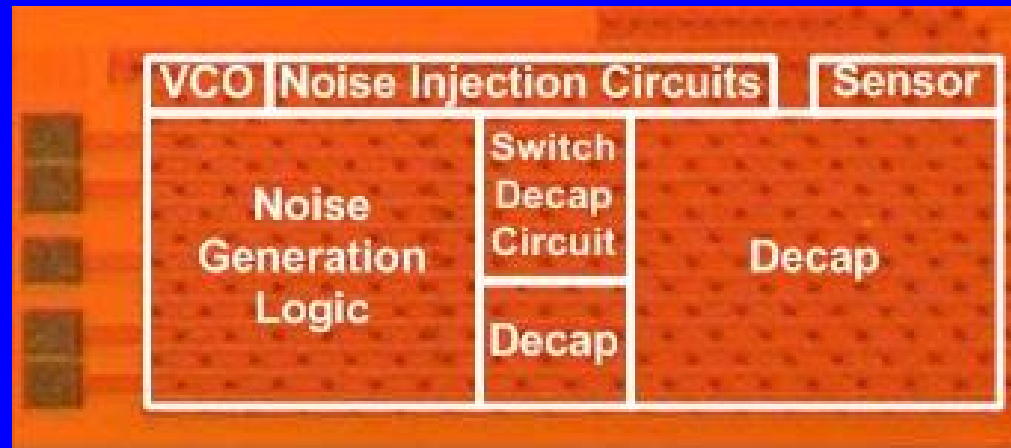
- **5–11X boost over passive decaps**
- **Equivalent to 0.1-1 $\Omega$  resistive damping**
- **Passive resistor aggravates IR drop**

# Performance Comparison

	Active Damping Ckt.*	This work
Technology	90nm	130nm
Static Current	2.42mA	0.54mA
Load Current suppressed	8.71mA (3X $I_{static}$ )	33mA (61X $I_{static}$ )
Regulator Area	59x20 $\mu\text{m}^2$	190x220 $\mu\text{m}^2$ (including 300pF)
First Droop Regulation	No	Yes
Analog Opamp	Yes	No

\* J. Xu et al., Intel, ISSCC 2007

# Die Photograph and Chip Summary



Technology	0.13 $\mu$ m Logic CMOS
Quiescent Current	0.54mA
Regulation Frequency	10–300MHz
Regulator Area (w/o decap)	100 $\mu$ m $\times$ 70 $\mu$ m
Regulator Area (w/ 300pF decap)	190 $\mu$ m $\times$ 220 $\mu$ m
Total Die Area	0.9mm $\times$ 1.8mm

- 9X less static current compared with prev. swdecap design
- Swdecap serves as passive decap under norm. condition
- Up to 11X decap boost compared with passive decap
- Negligible power consumed for decap switching (1.2%)



# Conclusions

- **Resonant supply noise impacts circuit performance and reliability**
- **A switched decap circuit is proposed**
  - **Low power resonant detection circuit**
  - **Digital-friendly implementation**
  - **Programmable and PVT insensitive switching threshold**
- **0.13 $\mu$ m test chip implemented**
  - **5–11X boost in effective decap value**
  - **Up to 9.8dB resonant noise suppression**
  - **9X reduction in static current compared with previous switched decap design**